PATENT PF-2200DIV

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant:

Yoshiaki YAMADA et al.

Appl. No.:

NEW

Group:

UNASSIGNED

Filed:

October 12, 2001

Examiner: UNASSIGNED

For:

OHMIC CONTACT PLUG HAVING AN IMPROVED CRACK FREE TIN BARRIER METAL IN A CONTACT

HOLE AND METHOD OF FORMING THE SAME

INFORMATION DISCLOSURE STATEMENT (SUBMISSION WITH CONTINUATION-IN-PART OR RULE 1.53(b) CONTINUATION OR DIVISIONAL APPLICATION)

Assistant Commissioner for Patents Date: October 12, 2001 Washington, DC 20231

Sir:

Pursuant to 37 C.F.R. §§ 1.97 and 1.98, applicant(s) hereby submit(s) an Information Disclosure Statement for consideration by the Examiner.

I. LIST OF PATENTS, PUBLICATIONS OR OTHER INFORMATION

The patents, publications, or other information submitted for consideration by the Office are listed on the PTO-1449 form(s), attached hereto.

REFERENCES PREVIOUSLY CITED OR SUBMITTED II.

37 C.F.R. § 1.98(d), consideration of Pursuant to information listed on the PTO-1449 form(s) is requested since any patents, publications, or other information which are listed on the PTO-1449 form(s) but for which copies are not enclosed herewith, were previously cited by or submitted to the PTO in one of the following applications which has been relied upon for an earlier filing date under 35 U.S.C. § 120:

U.S. Appl. No(s).

U.S. Filing Date(s)

09/197,682

November 23, 1998

III. FEES

This Information Disclosure Statement is being filed concurrent with the filing of a continuation-in-part, continuation, or divisional patent application; therefore, no fee is required.

If the Examiner has any questions concerning this IDS or requires a copy of any of the references cited but not provided, he/she is requested to contact the undersigned. If it is determined that this IDS has been filed under the wrong rule, the PTO is requested to consider this IDS under the proper rule (with a petition if necessary) and charge the appropriate fee to Deposit Account No. 25-0120.

If necessary, the Commissioner is hereby authorized in this, concurrent, and future replies, to charge payment or credit any overpayment to Deposit Account No. 25-0120 for any additional fee required under 37 C.F.R. §§ 1.16 or 1.17; particularly, extension of time fees.

Respectfully submitted,

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Βv

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LM/jrs PF-2200DIV

Enclosures:

□ PTO-1449

☐ References

☐ Foreign Search Report

☐ Other:

(Rev. 04/19/2000)

Form PTO-1449									PF-2200DIV	NEW	ON NO.		
INFORMATION DISCLOSURE CITATION IN AN APPLICATION									Yoshiaki YAMADA	et al.		S. T. S.	
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considered.	Include copy	of t	his f	orm w	ith ne	ext co	mmunicatio	on to applicant.					